

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Q _g Typ	I _D Max T _C = +25°C (Note 10)
40V	3mΩ @ V _{GS} = 10V	83nC	100A
	5mΩ @ V _{GS} = 4.5V	35nC	100A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**
- PPAP Capable (Note 4)**

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

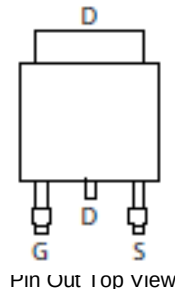
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters
- Motor Control

Mechanical Data

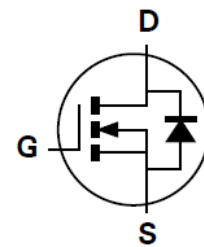
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top view



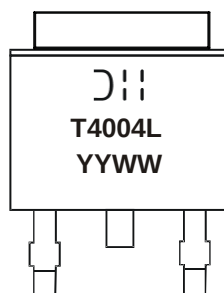
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH4004LK3Q-13	TO252	2,500/Tape & Reel

- Notes:
- EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



= Manufacturer's Marking
 T4004L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 16 = 2016)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	T _C = +25°C (Note 10)	I _D	100	A
	T _C = +100°C		100	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	200	A
Maximum Continuous Body Diode Forward Current (Note 7)		I _S	100	A
Avalanche Current, L = 0.2mH		I _{AS}	30	A
Avalanche Energy, L = 0.2mH		E _{AS}	90	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	3.9	W
Thermal Resistance, Junction to Ambient (Note 6)		R _{θJA}	38	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P _D	180	W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	0.8	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.4	3	mΩ	V _{GS} = 10V, I _D = 50A
		—	4	5	mΩ	V _{GS} = 4.5V, I _D = 50A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 50A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iSS}	—	4,450	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	1,407	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	74	—	pF	
Gate Resistance	R _g	—	0.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	35	—	nC	V _{DS} = 20V, I _D = 30A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	83	—	nC	
Gate-Source Charge	Q _{gs}	—	10	—	nC	
Gate-Drain Charge	Q _{gd}	—	11.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.9	—	ns	V _{GS} = 10V, V _{DS} = 20V, R _G = 1.6Ω, I _D = 30A
Turn-On Rise Time	t _r	—	13.2	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	25.8	—	ns	
Turn-Off Fall Time	t _f	—	7.9	—	ns	
Body Diode Reverse Recovery Time	t _{rr}	—	48	—	ns	I _F = 50A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	72	—	nC	I _F = 50A, di/dt = 100A/μs

- Notes:
- Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions while operating in a steady state.
 - Thermal resistance from junction to solder point (on the exposed drain pin).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.
 - Package Limited.

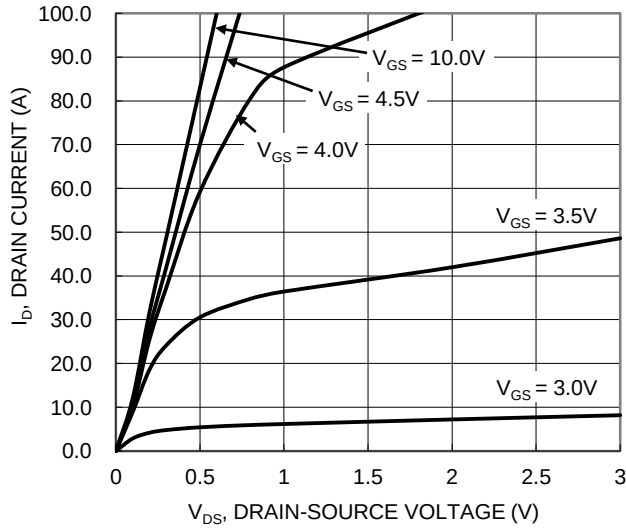


Figure 1. Typical Output Characteristic

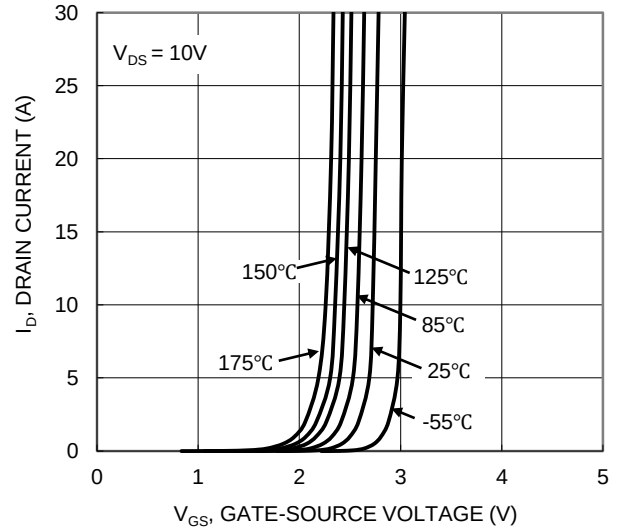


Figure 2. Typical Transfer Characteristic

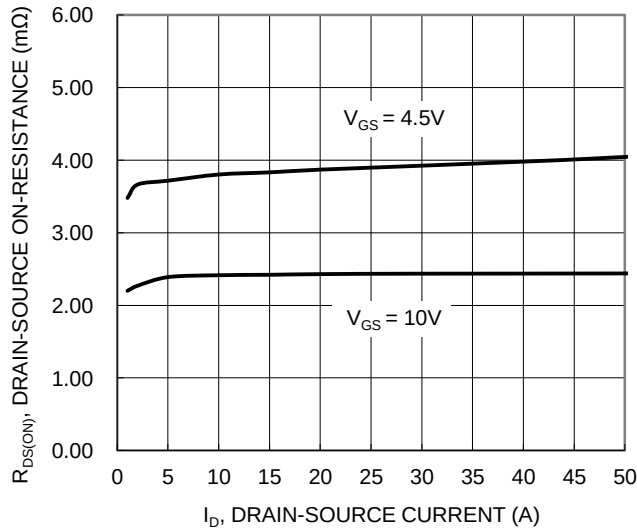


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

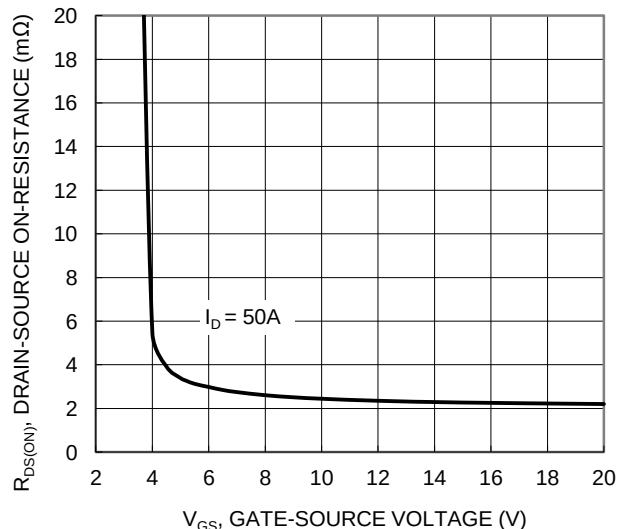


Figure 4. Typical Transfer Characteristic

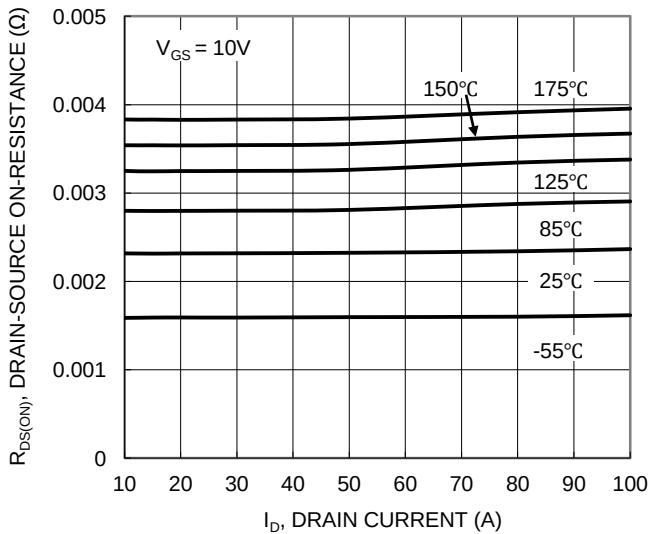


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

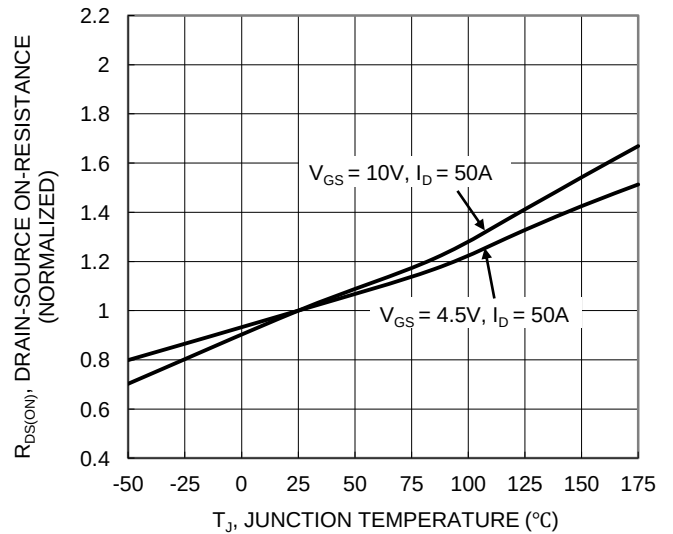
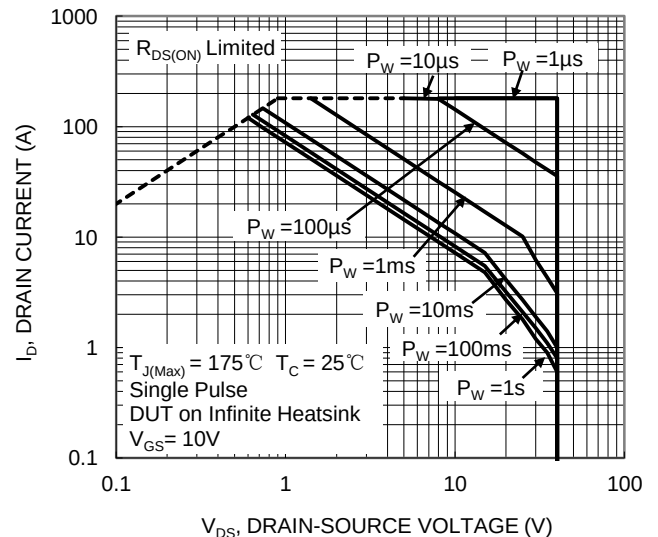
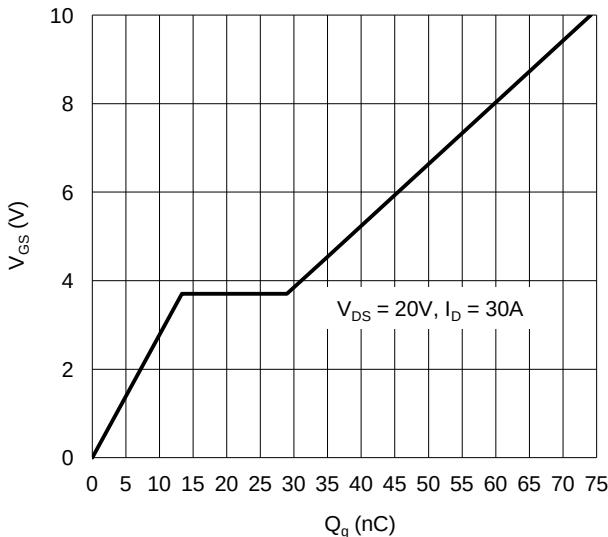
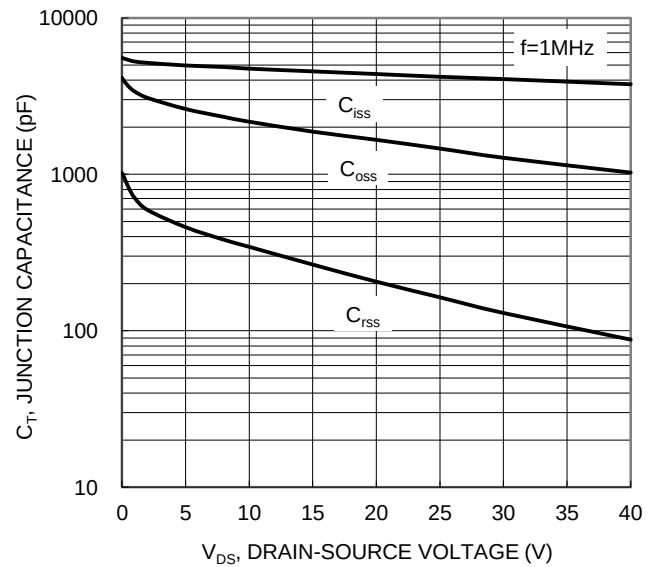
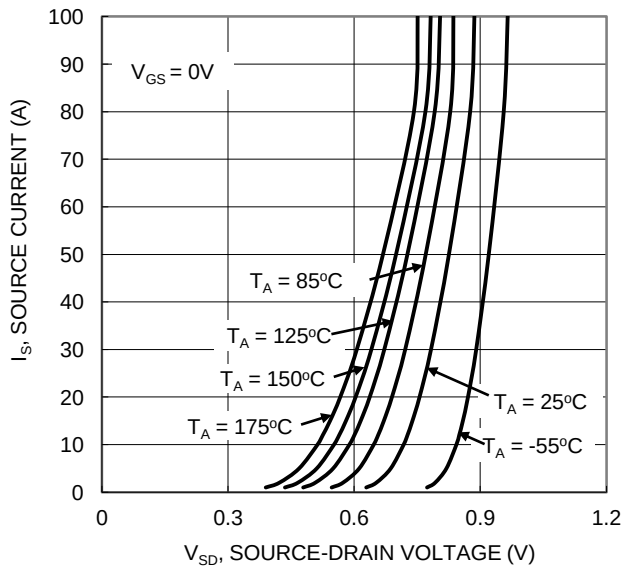
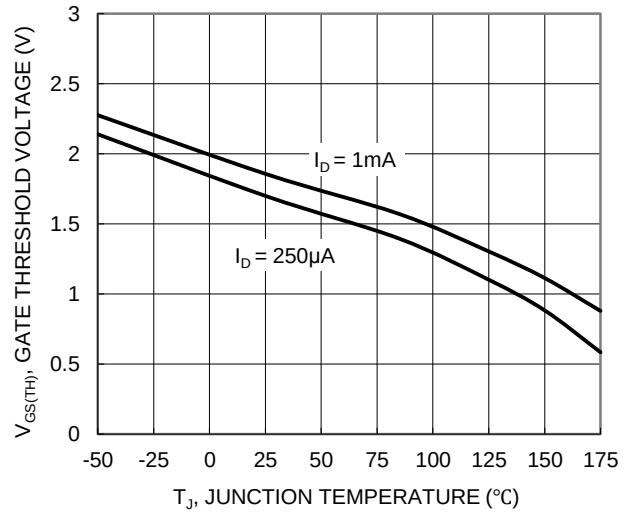
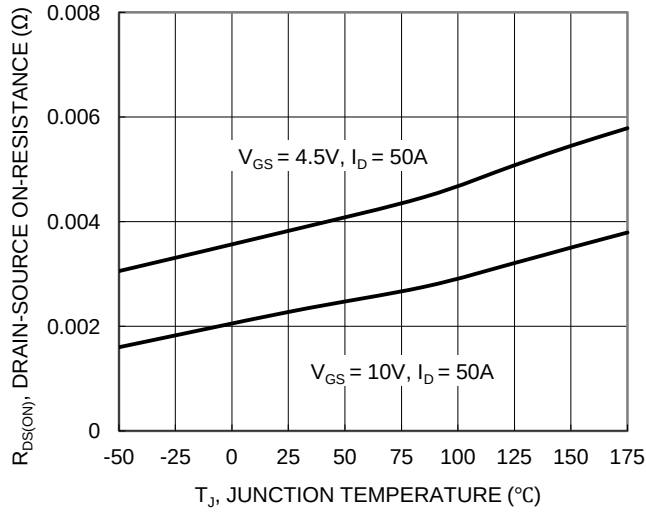


Figure 6. On-Resistance Variation with Temperature



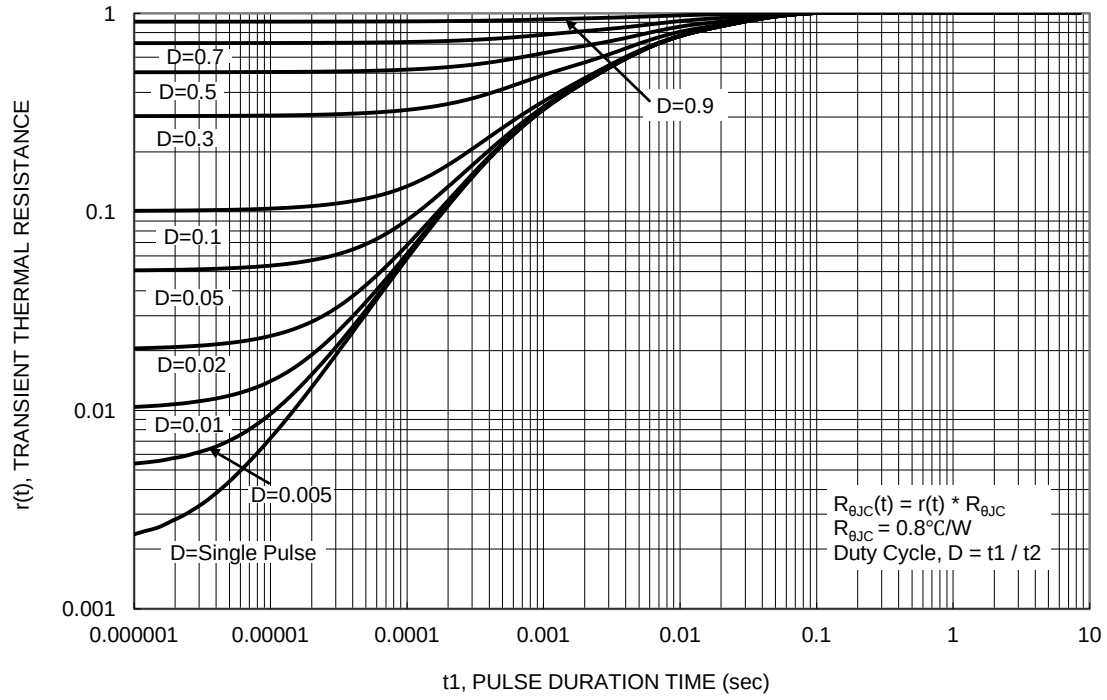
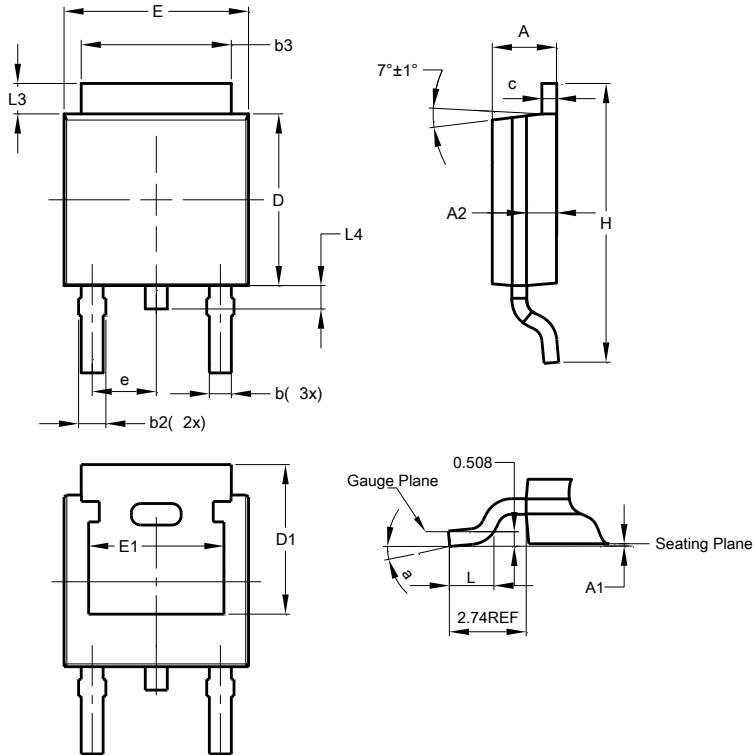


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

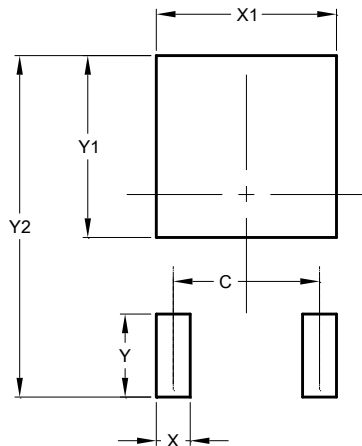


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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